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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of : Confirmation No. 9191  
Makoto AKIZUKI et al. : Docket No. 2001-1897  
Serial No. 10/025,899 : Group Art Unit 1762  
Filed December 26, 2001 : Examiner B. Pianalto

METHOD FOR FORMING GAS CLUSTER  
AND METHOD FOR FORMING THIN FILM

THE COMMISSIONER IS AUTHORIZED  
TO CHARGE ANY FEES OR EXPENSES IN THE  
FEE PAYMENT ON THIS DOCUMENT TO AN ESQ.  
ACCT. NO. 10000000000000000000

**RESPONSE**

Assistant Commissioner for Patents,  
Washington, D.C.

Sir:

In response to the Official Action dated August 7, 2002, the period for response having been extended for three months by the attached petition, please amend the present application as follow:

**IN THE CLAIMS:**

**Claims 15-18, cancel without prejudice to the subject matter thereof.**

**Kindly amend the following claim:**

1. (Amended) A method for forming a gas cluster which comprises the steps of mixing a substance liquid at room temperature under atmospheric pressure and a pressurized gas, and causing the resultant mixture to spout as a gas from a nozzle to generate a cluster which is a lumpy group of atoms or molecules.

11. (Amended) A method for forming a thin film, which comprises the steps of forming a cluster which is a lumpy group of atoms or molecules of a reactive substance gaseous at room temperature, irradiating cluster ions ionized therefrom onto a substrate surface, and at the same time